



Building Tracking Detector Modules for P2



KPH-Meet-up 09-05-2023

Lucas Sebastian Binn

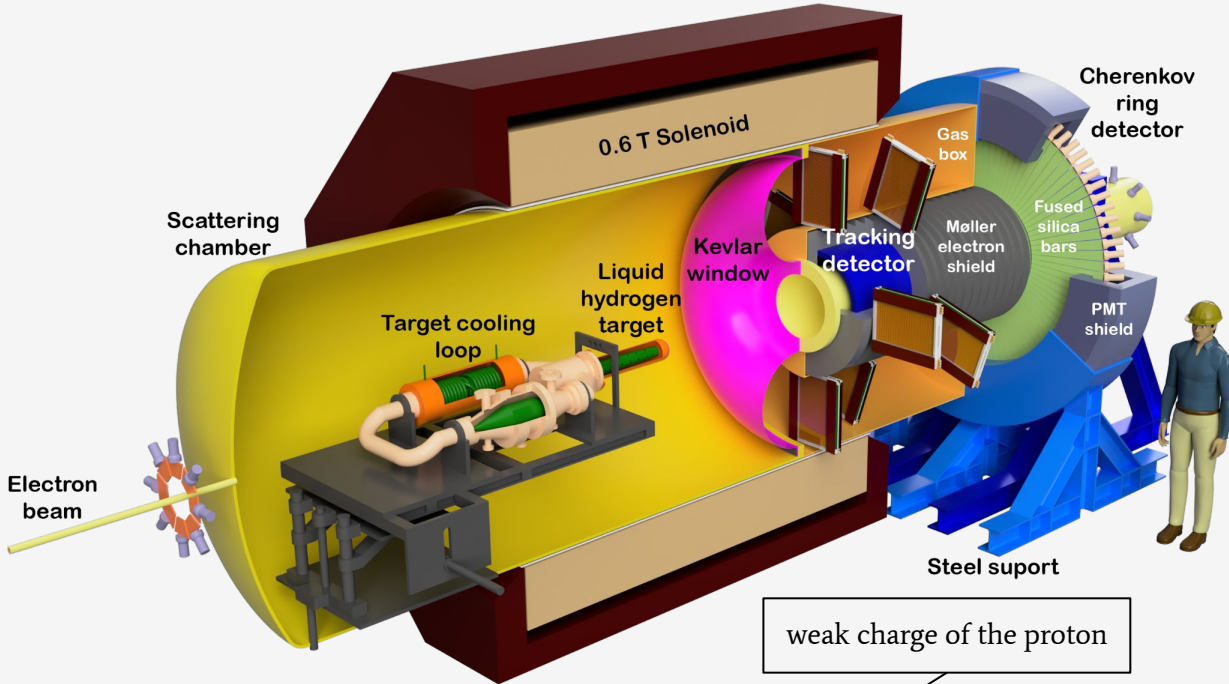
AG Berger

Niklaus Berger, Philipp Kern,

Michail Kravchenko, Lars Steffen Weinstock



P2 Experiment

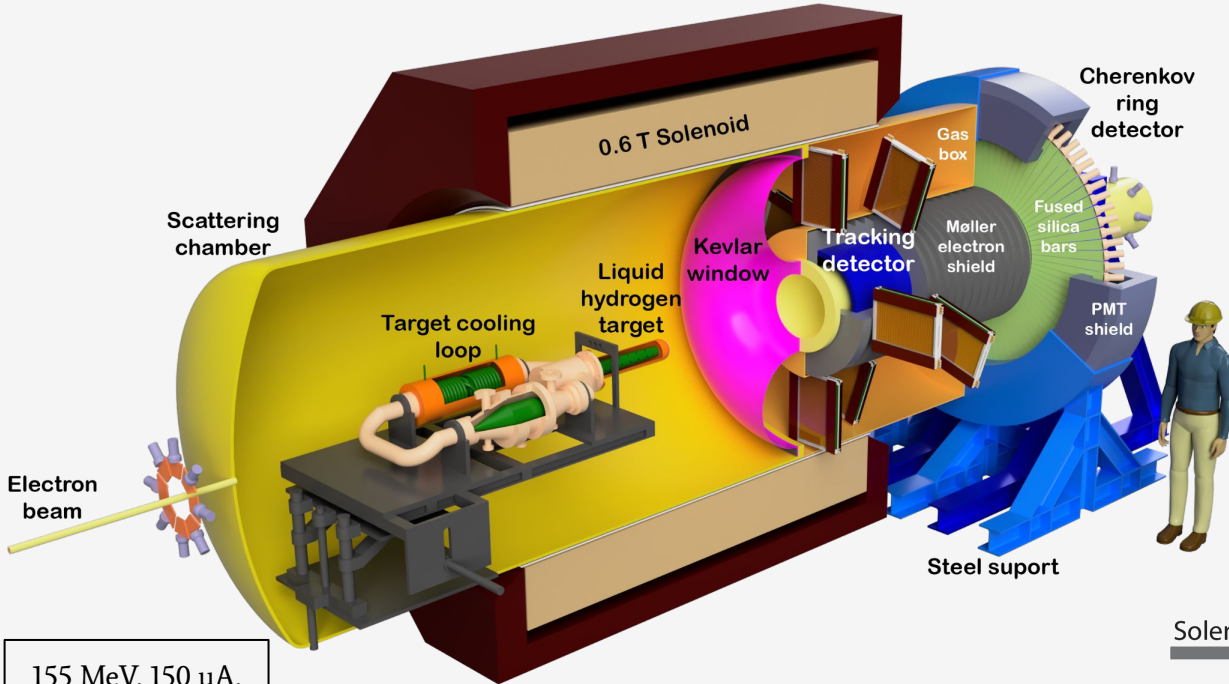


- Located @ MESA
- Determination of weak mixing angle at low momentum transfer
- Measure parity violating asymmetry in elastic electron-proton scattering

$$A_{PV} = \frac{\sigma_L - \sigma_R}{\sigma_L + \sigma_R} = \frac{G_F Q^2}{4\sqrt{2}\pi\alpha} (Q_W + F(Q^2))$$

$$Q_W = 1 - 4 \sin^2 \theta_W$$

P2 Experiment

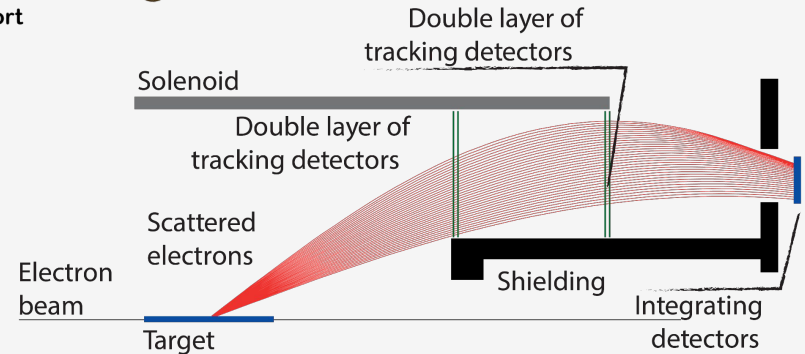


- Located @ MESA
- Determination of weak mixing angle at low momentum transfer
- Measure parity violating asymmetry in elastic electron-proton scattering
- Tracking Detector
 - Determination of average momentum transfer Q^2
 - Study of systematic effects

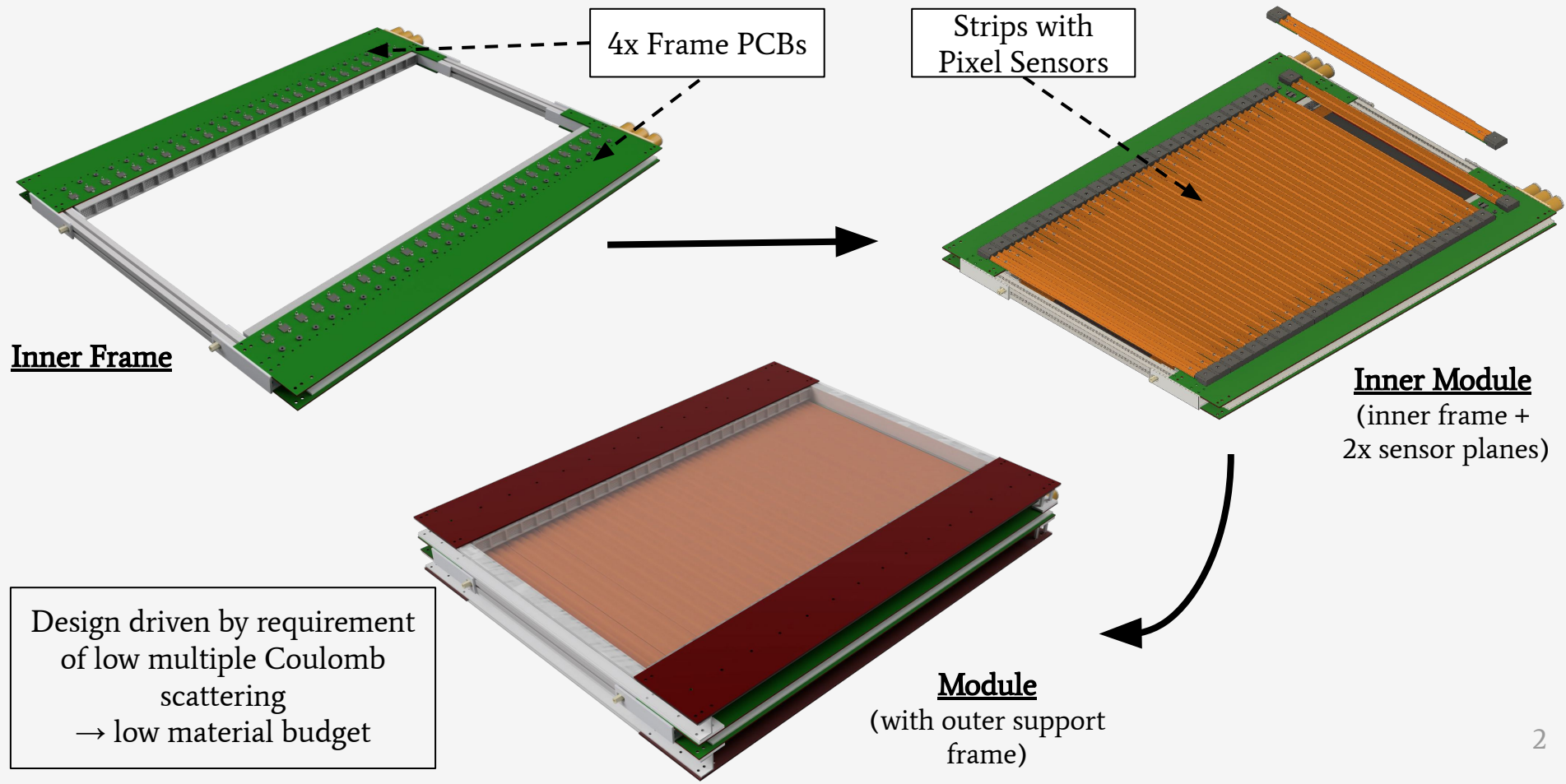
155 MeV, 150 μA ,
 $f_{\text{sw}} = 1 \text{ kHz}$

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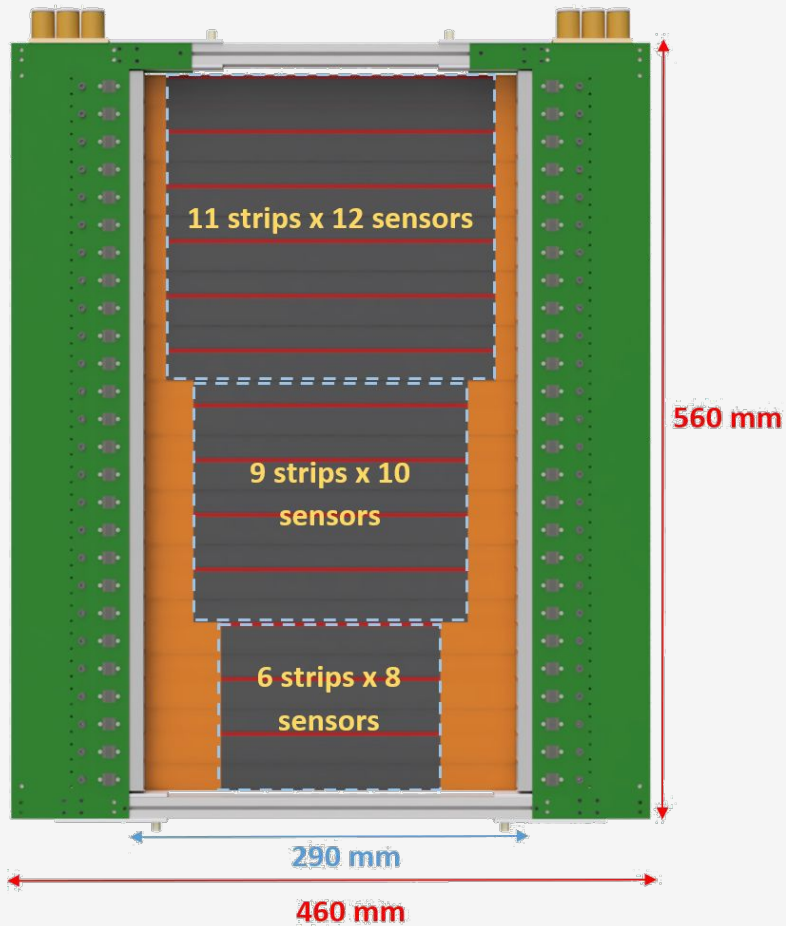
$$Q_W = 1 - 4 \sin^2 \theta_W$$



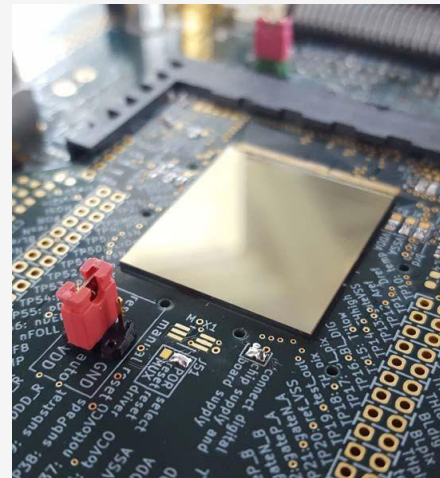
Tracking Detector Module



Strip Configurations & Sensors

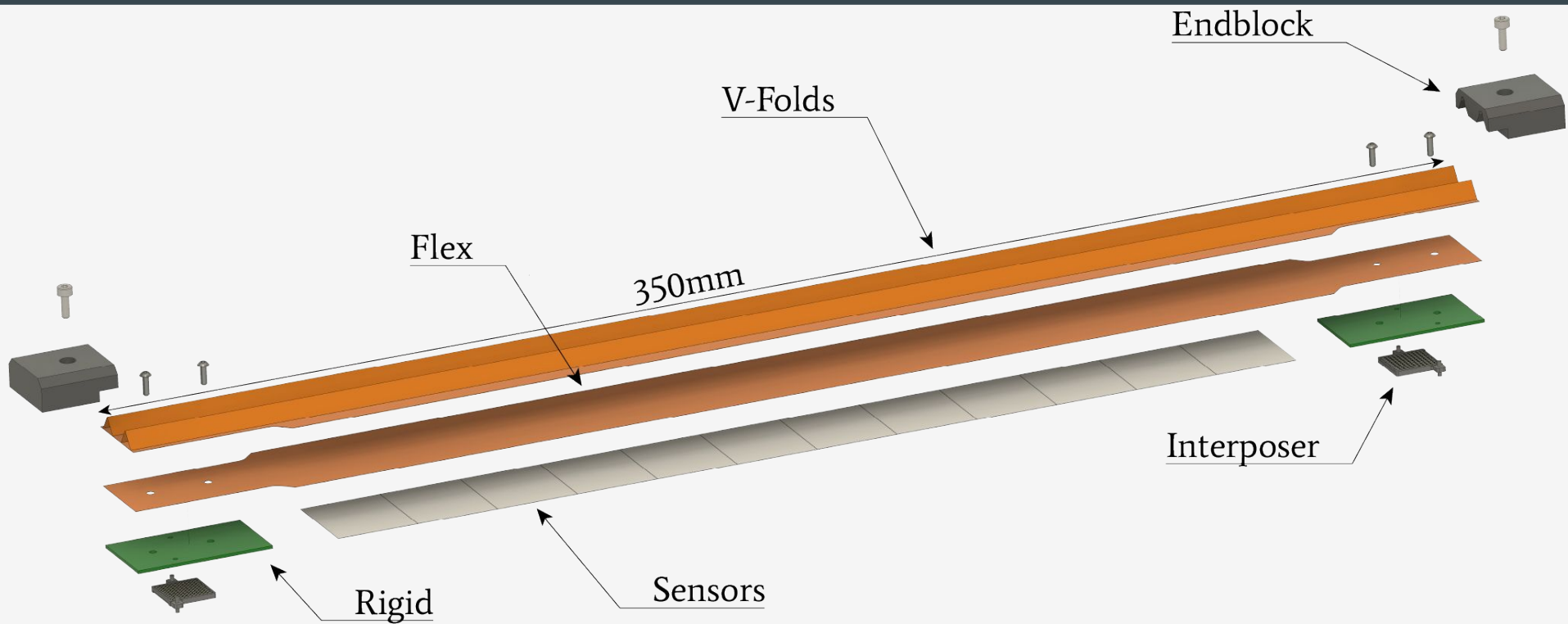


- 540 pixel sensors per module
- Similar pixel sensors as used in the Mu3e experiment
→ knowledge in group
- Monolithic, 70 μm thickness
→ reduced material budget
→ reduced multiple Coulomb scattering

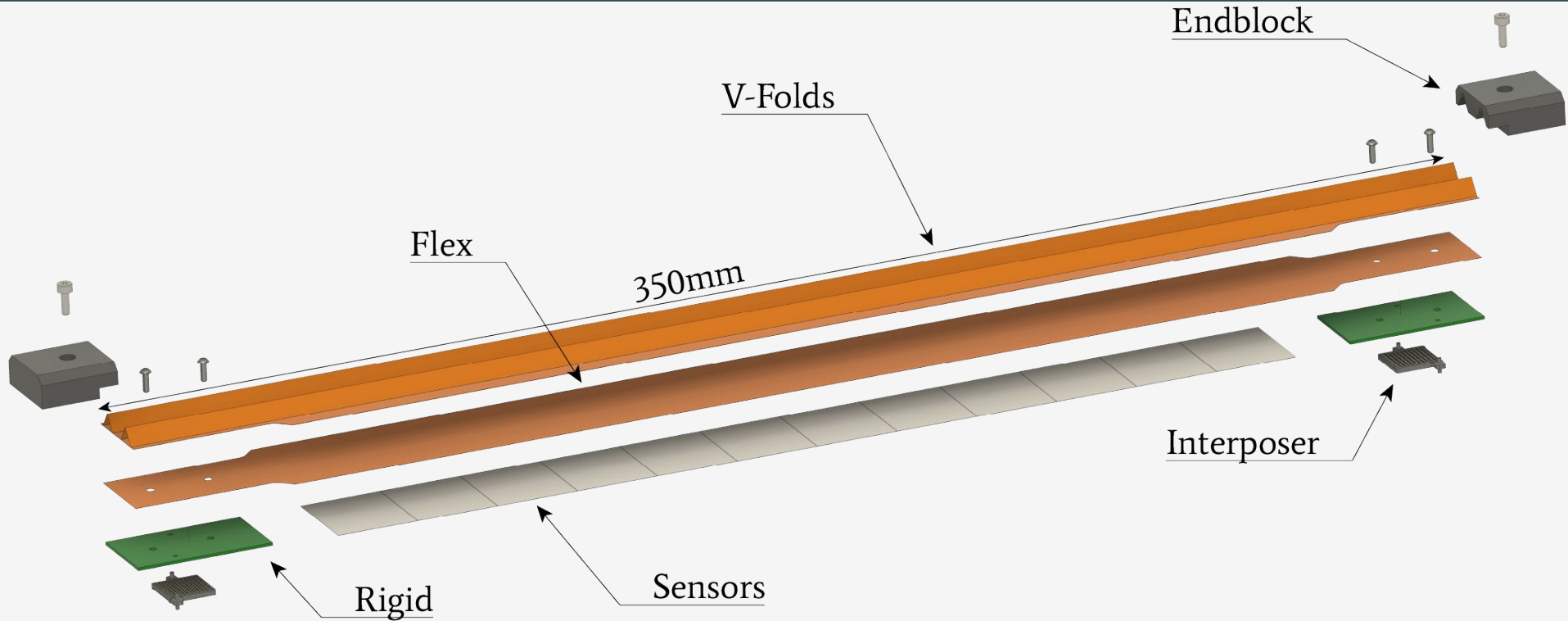


[MuPix 10]

Structure of the Strips



Structure of the Strips



- Two layer flex (with rigid parts at the ends)
- 9 μm copper thickness, 25 μm dielectric $\rightarrow X_0 = 1.45\%$

Development of Rigid-Flex

Soldered Rigid-Flex

Rigid-Flex

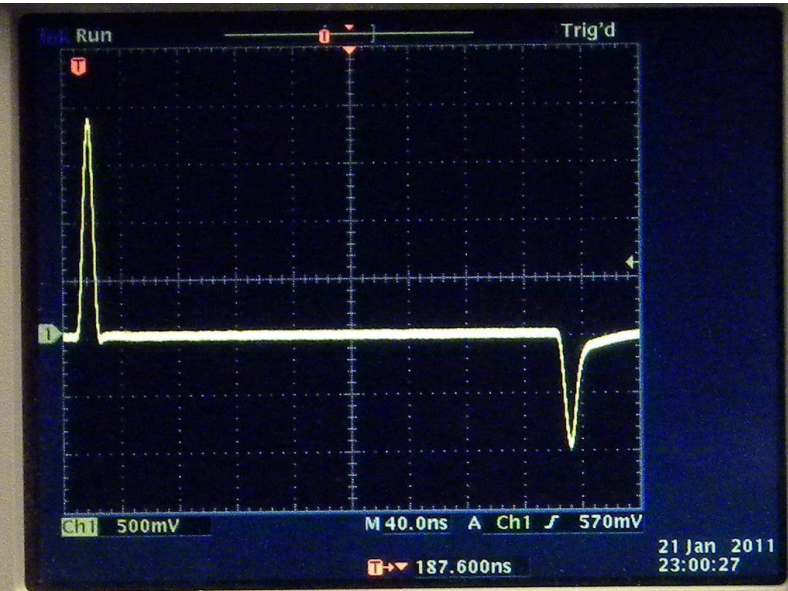
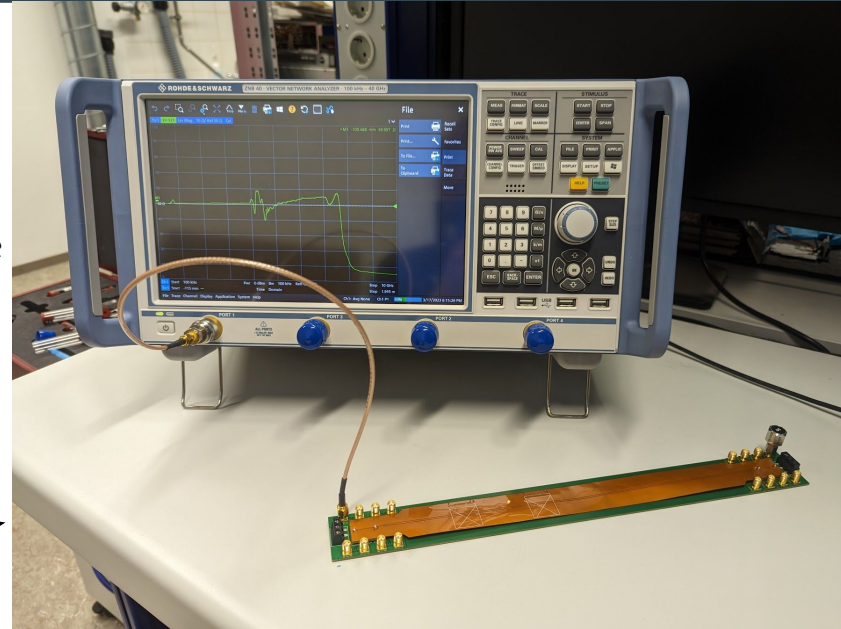


Test Jig (with mounted rigid-flex)



Time Domain Reflectometry

- Measure characteristic impedance along conductor
- Verify differential line impedance (constant) (signal integrity @ 1.25 Gbit/s)
- Reflection of signal at change of characteristic impedance



[Oscilloscope]

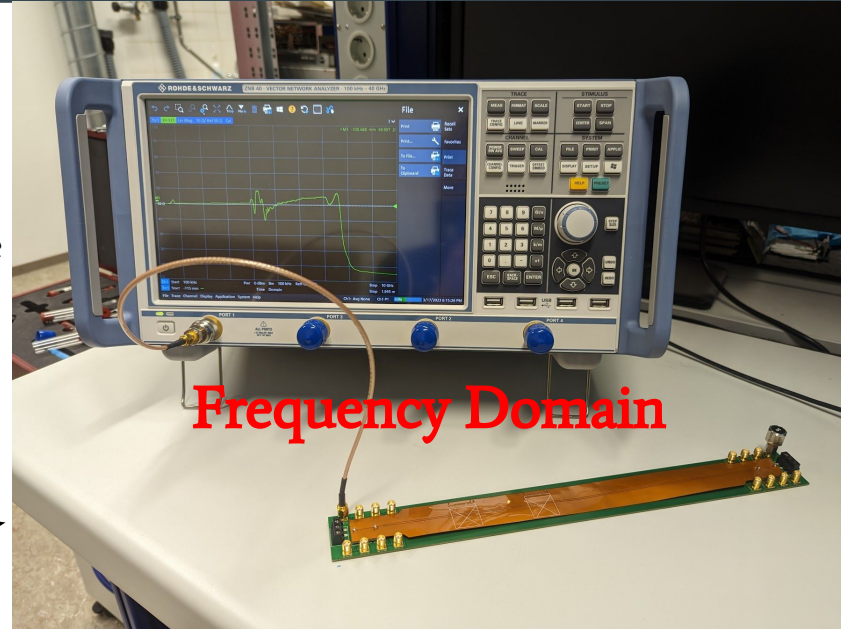
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[Oscilloscope]

DFT



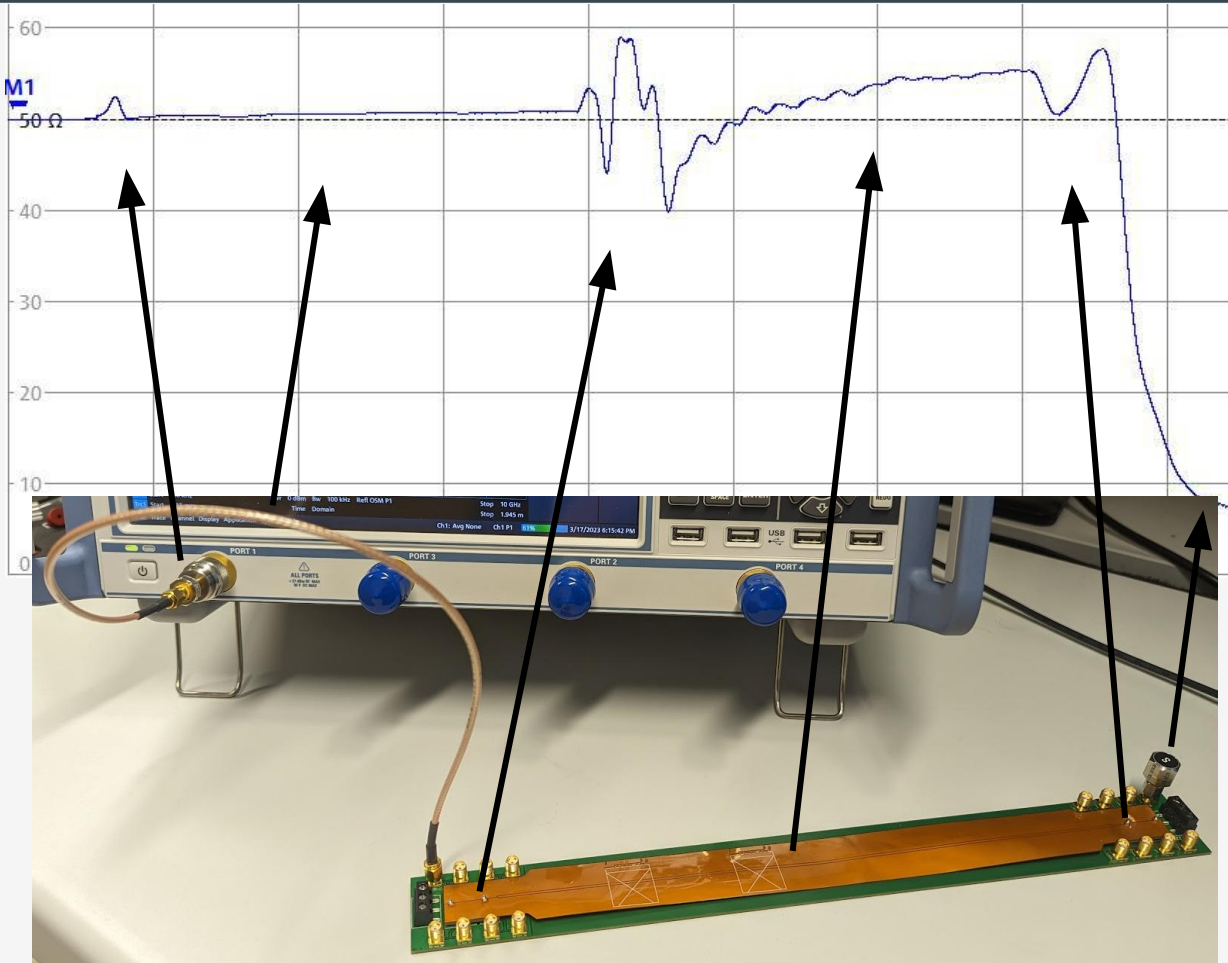
[Vector Network Analyser]

Time Domain Reflectometry



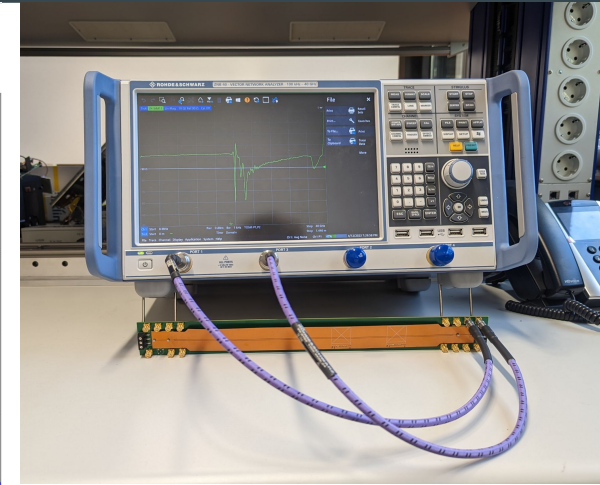
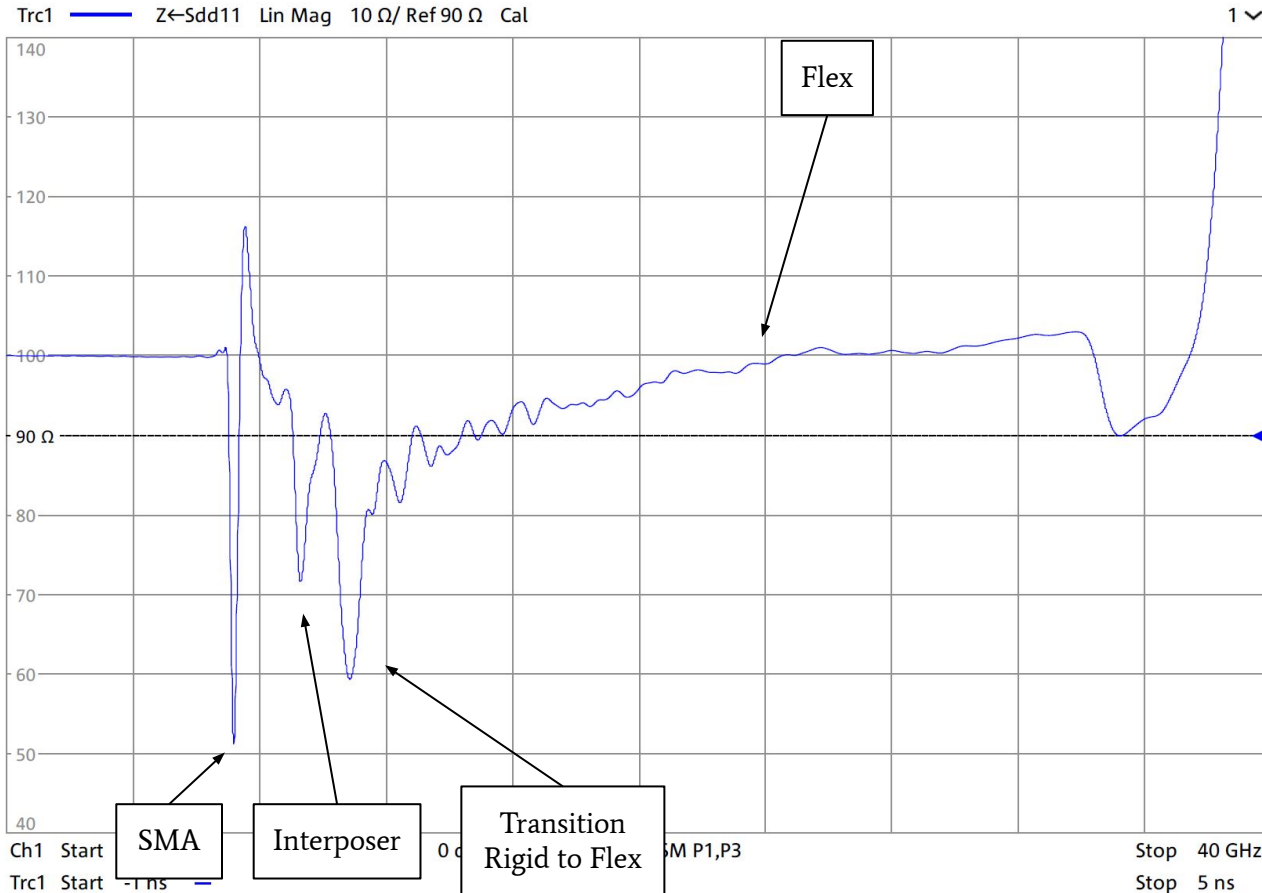
Time Domain Reflectometry

Characteristic Impedance



Time Domain Reflectometry

4/18/2023 3:54:59 PM
1311.6010K84-101739-qA

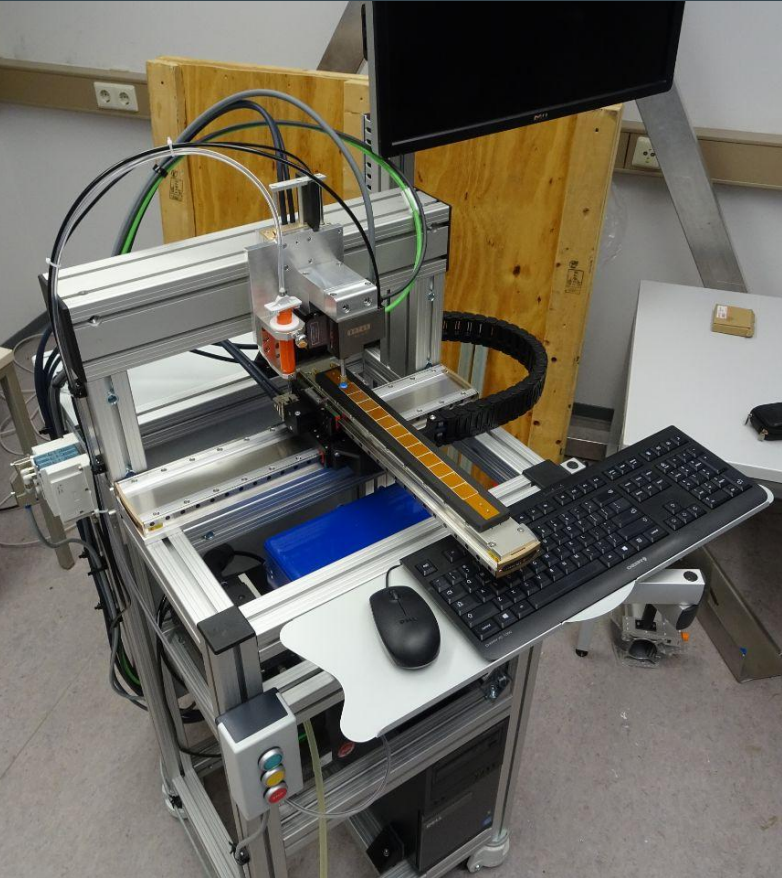


Next up
Bit Error Rate Test
+ Eye Diagrams

Gluing & Bonding of Sensors

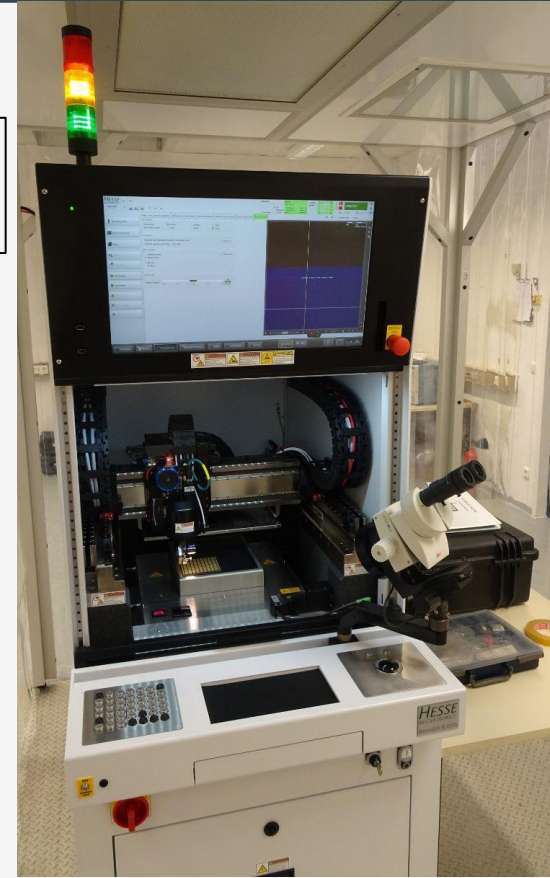
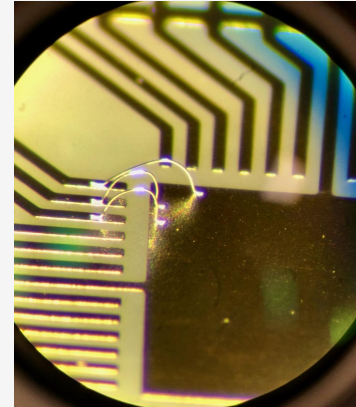


Gluing & Bonding

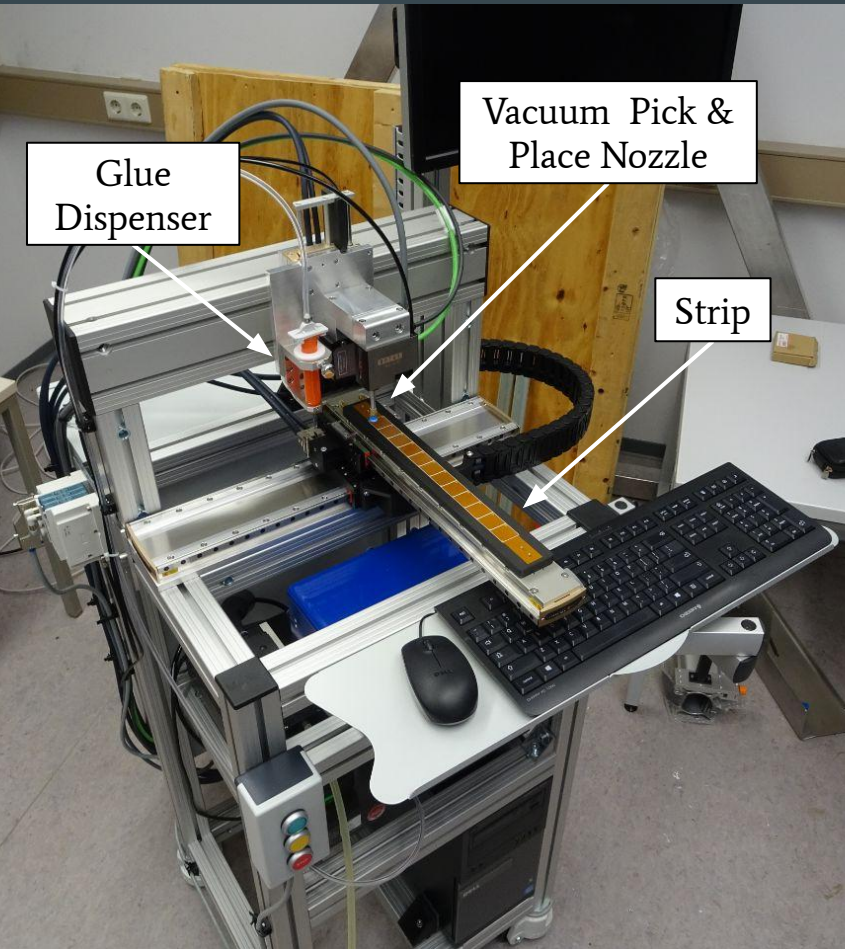


Gluebot

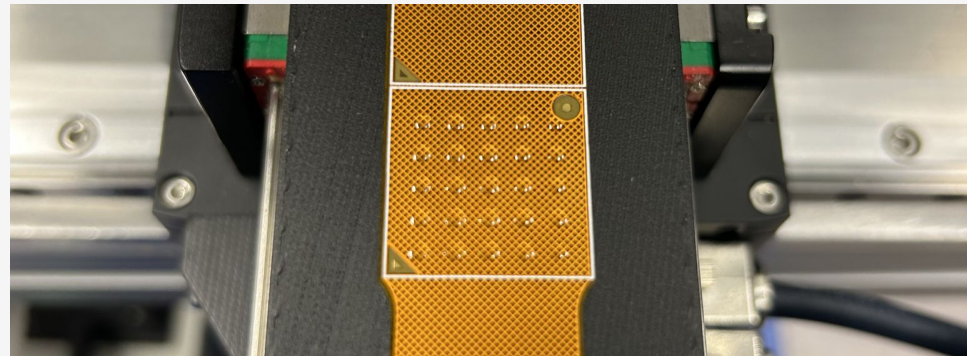
Production of all 260 strips in Mainz
→ semi-automated processes



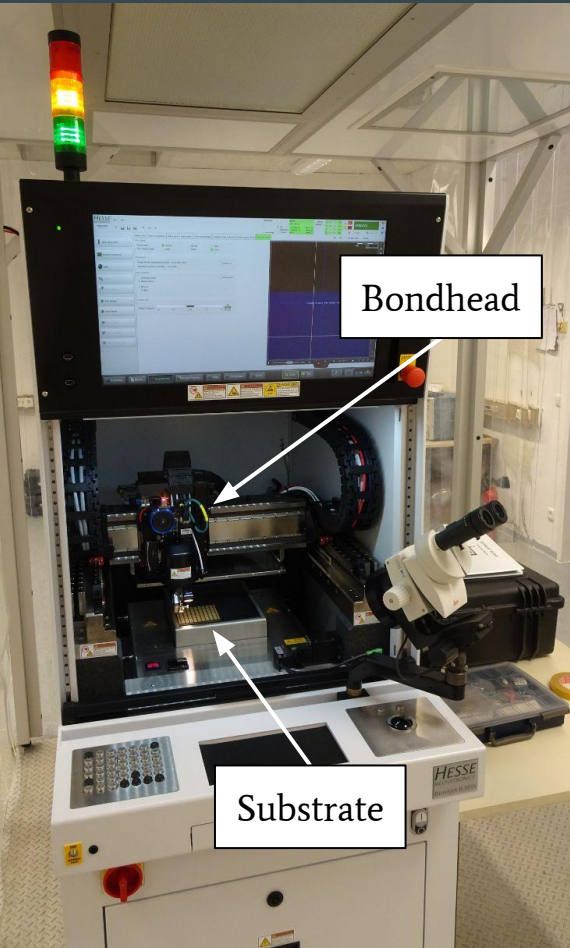
Wire-Bonding Machine 9



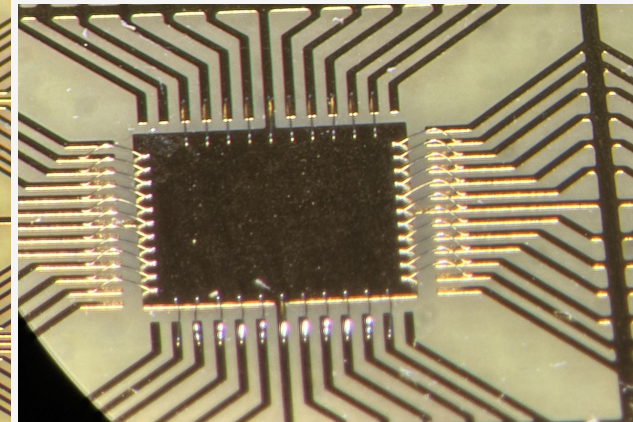
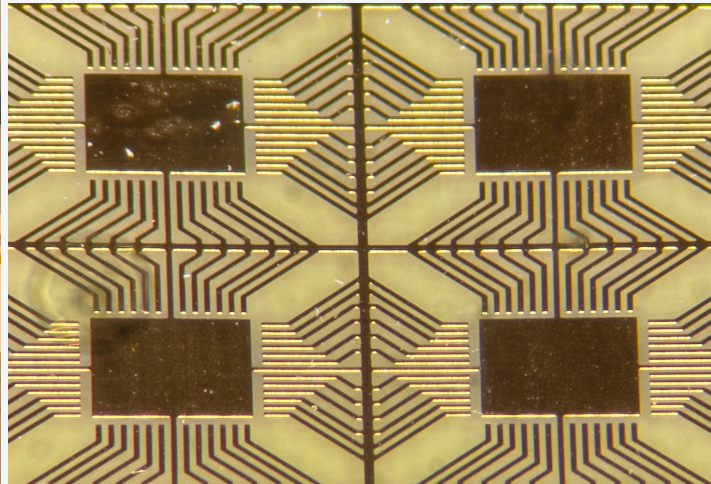
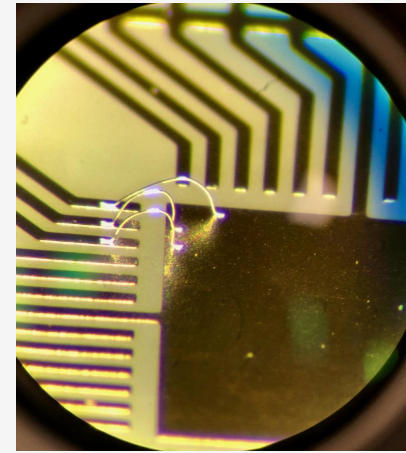
- Build & Developed by us
- Features
 - 4 Axes CNC Machine
 - Vacuum Table
 - Time Pressure Dispenser
 - Vacuum Pick & Place Nozzle
 - Microscopic Camera
 - Laser Distance Sensor
 - UV LEDs for Curing
- Sensor Placement Precision Goal $\sim 10 \mu\text{m}$



Wire Bonding Machine



- Commercial Machine
- Ultrasonic Wedge Bonding (cold welding)
- Aluminium Wire 25 μm
- Pattern Recognition
- Speed ~ 3 wire bonds / s



Conclusion & Outlook



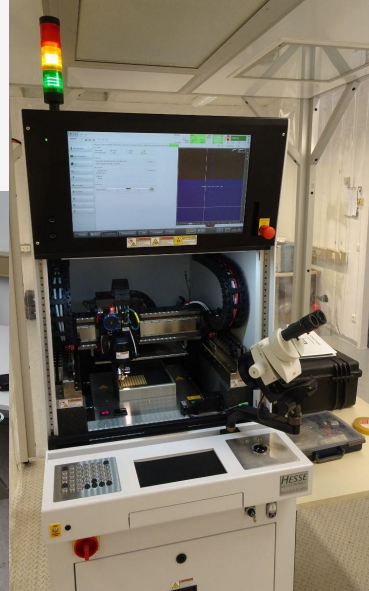
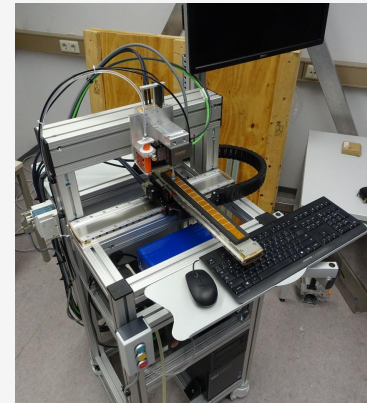
Rigid-Flex

- Developing Testing Methods
- Time Domain Reflectometry for understanding
- Bit Error Rate Test & Eye Diagram (signal integrity)



Gluing & Wire Bonding

- Glue Dispensing & Wire Bonding parameters
- Gluebot Picking & Placing of Sensors
- Semi-automation of processes (pattern recognition etc.)



Conclusion & Outlook



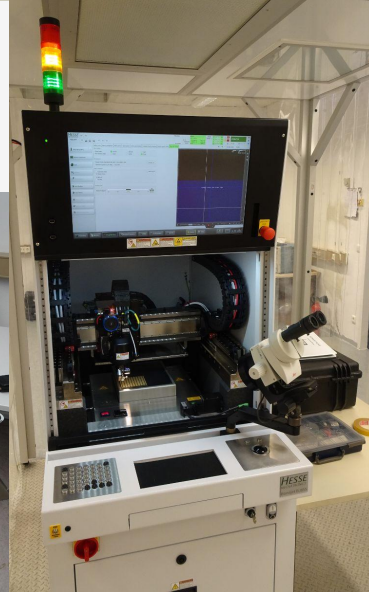
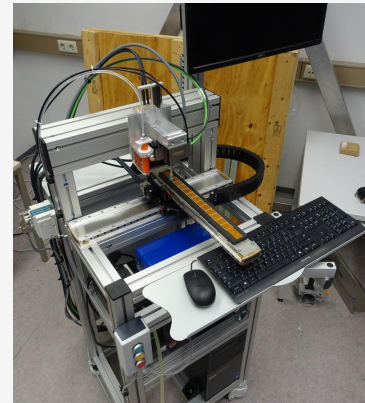
Rigid-Flex

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Gluing & Wire Bonding

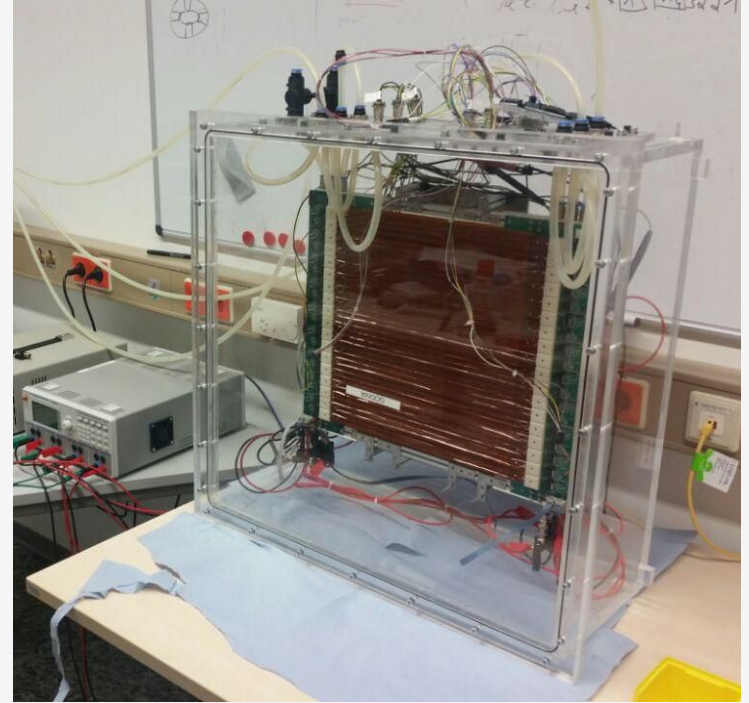
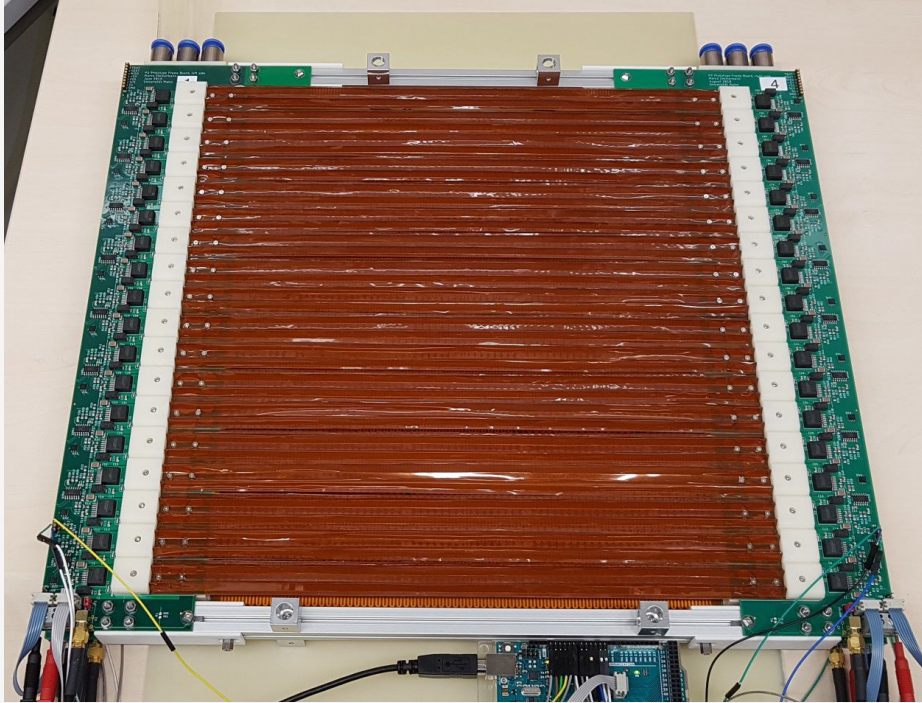
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Thanks for your attention!



Backup

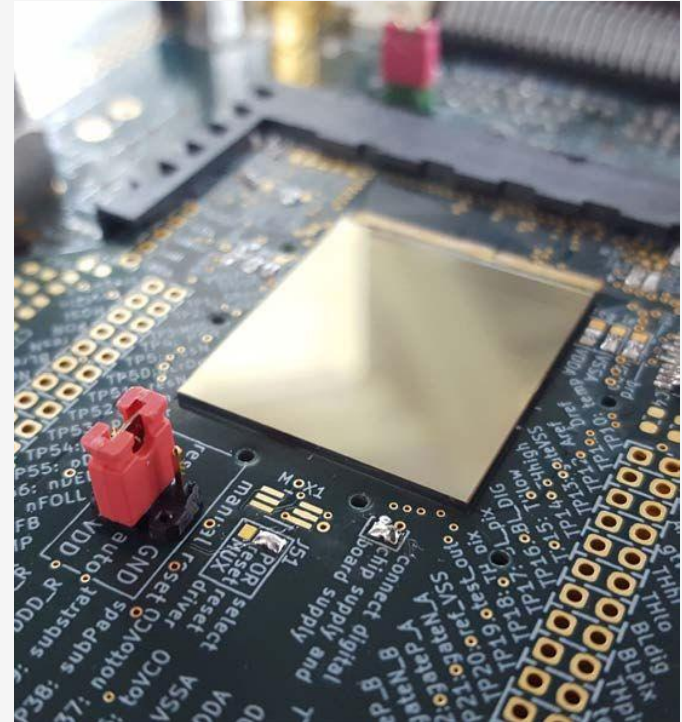
Thermo Mechanical Prototype



[Marco Zimmermann & Michail Kravchenko]

MuPix 10

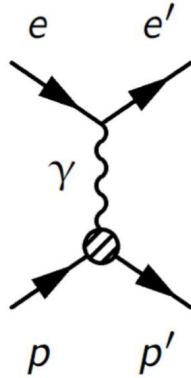
- HV-MAPS - High voltage monolithic active pixel sensors (Ivan Perić)
- Based on 180 nm HV-CMOS process
- Can be thinned down to 50 μm
- Pixel Matrix 256 x 250
- Pixel Size 80 μm x 80 μm
- Active Area 20.40 mm x 20 mm
- Efficiency > 99%
- Noise Rate < 2 Hz / Pixel
- Power Consumption < 200 mW / cm^2



P2 - Theory

The weak mixing angle
(Weinberg-angle):

$$\sin^2 \theta_W = \frac{g'^2}{g^2 + g'^2}$$

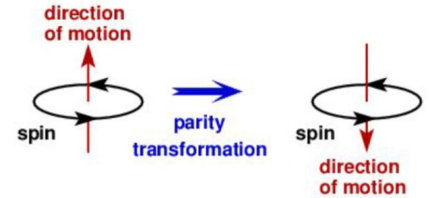


Proton electric charge
+1



Proton weak charge
 $1 - 4 \sin^2 \theta_W$

Violates parity!



Parity violating asymmetry

momentum transfer

Asymmetry:
$$A_{PV} = \frac{G_F Q^2}{4\sqrt{2}\pi\alpha} \left(1 - 4 \sin^2 \theta_W - F(Q^2) \right)$$

proton form factor
(small @ low Q^2)

P2 - Experiment

Measuring the parity violating asymmetry in e-p-scattering

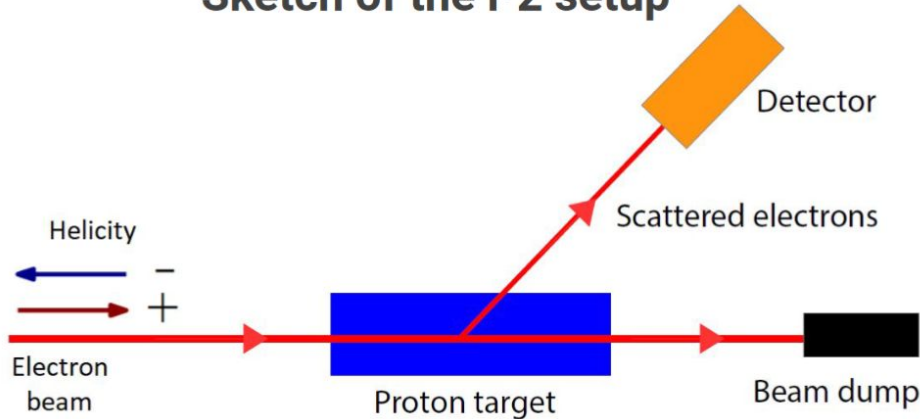
polarization of the beam

$$A_{exp} \equiv \frac{N^+ - N^-}{N^+ + N^-} = P_{beam} \cdot \langle A_{pv} \rangle + A_{app} \sim \underline{30 \text{ ppb}}$$

averaged expected value

apparative asymmetry

Sketch of the P2 setup



Beam:

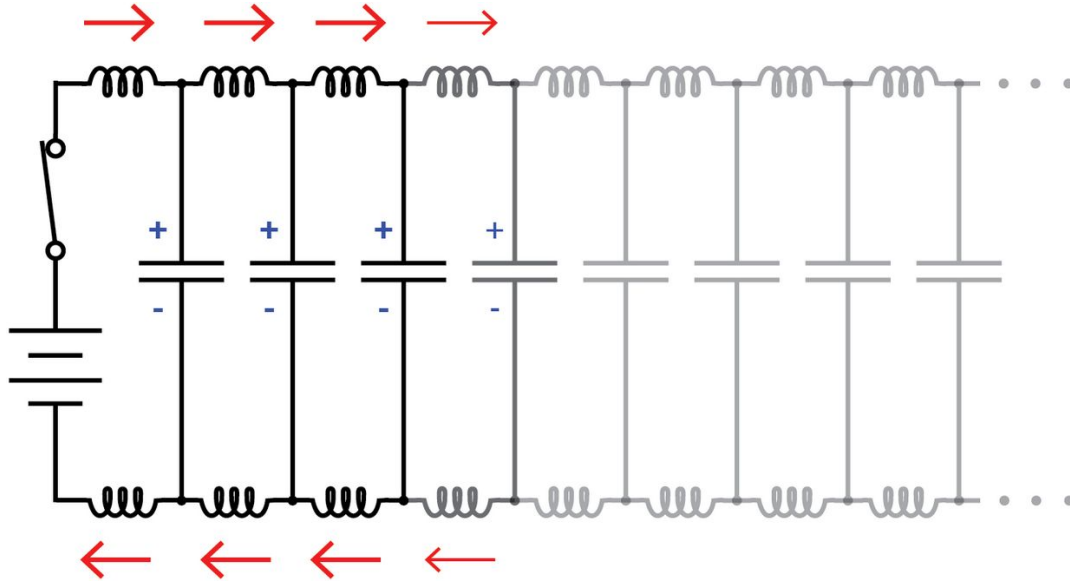
- Highly polarized ($\geq 85\%$)
- Current: $150 \mu\text{A} = 10^{15} \text{ e}^-/\text{s}$
- $L \approx 2.4 \cdot 10^{39} \text{ cm}^{-2}\text{s}^{-1}$
- Energy: 155 MeV
- Flip helicity @ 1 kHz

Additional requirement:

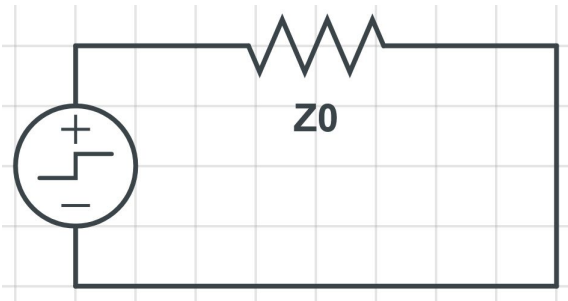
- Beam polarization:
 $\Delta P_b / P_b \leq 0.5\%$

Characteristic Impedance

$$I = C \cdot \frac{dU}{dt}$$
$$U = L \cdot \frac{dI}{dt}$$



$$v = \frac{c}{\sqrt{L' C'}}$$



$$Z_0 = \frac{v}{I} = \sqrt{\frac{L'}{C'}}$$

2-Port VNA

Params

Ratios

Wave

Z←Sij

Z←S11 Z←S12

Z←S21 Z←S22

Trace Config

Time Domain

Type Low Pass Step

Low Pass Settings...

Impulse Response Arbitrary Sidelobes...

Side Lobe Level 70 dB

Resolution Enh. 1

TD-VSWR

Gate Span 524.6 mm

Show Impulse Response...

Traces

Mem

All Mem All Data

Math

Time Domain

Time Gate

Trace Statistics

Smooth Shift Hold

Infinite Averaging

Trace Data

$$S_{11} = |S_{11}| \cdot e^{i\phi}$$

$\frac{V_{refl}}{V_{in}}$ →

← phase delay

$$|S_{11}| = 20 \cdot \log \left(\left| \frac{V_{refl}}{V_{in}} \right| \right)$$

$$= \frac{Z - Z_0}{Z + Z_0}$$

new impedance ↑

reference impedance ↑

